

CLAIMS

1. A photosensitive resin composition comprising (a) a binder polymer based on a copolymer containing benzyl
5 (meth)acrylate as a building block, (b) a photopolymerizable compound having at least one polymerizable ethylenically unsaturated group in the molecule and (c) a photopolymerization initiator based on a hexarylbisimidazole compound.
2. The photosensitive resin composition according to claim
10 1, wherein component (a) is a (meth)acrylic acid/benzyl (meth)acrylate copolymer.
3. The photosensitive resin composition according to claim 2, wherein the polymerization ratio of (meth)acrylic acid to benzyl (meth)acrylate ranges from 5:95 to 50:50.
- 15 4. The photosensitive resin composition according to claim 1, wherein component (b) is at least one compound selected from the group consisting of compounds having a bisphenol skeleton, compounds obtained by reacting glycidyl group containing compounds with α,β -unsaturated carboxylic acids and
20 compounds obtained by reacting polyols with α,β -unsaturated carboxylic acids or lower alkoxyated derivatives thereof.
5. The photosensitive resin composition according to claim 1, wherein component (b) is at least one compound selected from the group consisting of 2,2-bis[4-
25 {(meth)acryloxypolyethoxy]phenyl]propanes (the number of ethoxy groups: 2-14), triglycerol di(meth)acrylate and ethoxy-
lated polypropylene glycol di(meth)acrylate.
6. The photosensitive resin composition according to claim

1, which further contains (d) a light-initiated color former.

7. The photosensitive resin composition according to claim

6, wherein component (d) is a triphenylmethane color former.

8. A photosensitive dry film prepared by applying to a

5 support film the photosensitive resin composition according

to any one of claims 1-7, drying the applied composition to

form a photosensitive resin layer and overlying the photosen-

sitive resin layer with a protective film.

9. The photosensitive dry film according to claim 8,

10 wherein the support film has a surface roughness (Ra) of no

more than 10 nm and a surface resistivity of no more than 10^{12}

Ω .